MURJ1220CT

Rev.E Mar.-2016

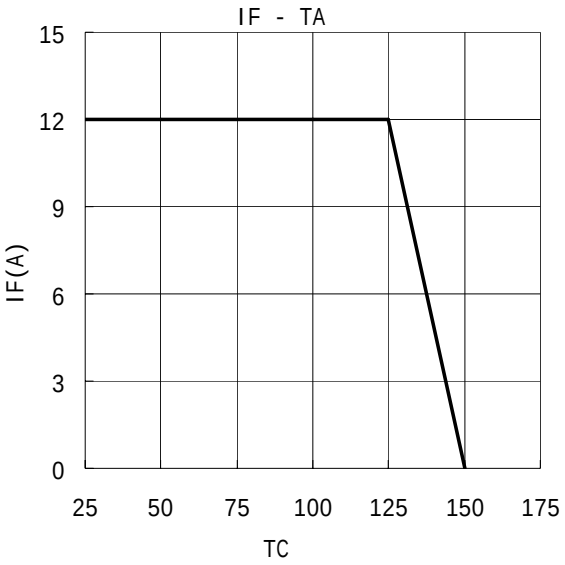
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Rectified Forward Current	I_F	2×6	A
Non Repetitive Peak Surge Current	I_{FSM}	100	A
Thermal Resistance Junction to Case	R_{Jc}	2.9	/W
Storage Temperature Range	T_j T_{stg}	-55 150	

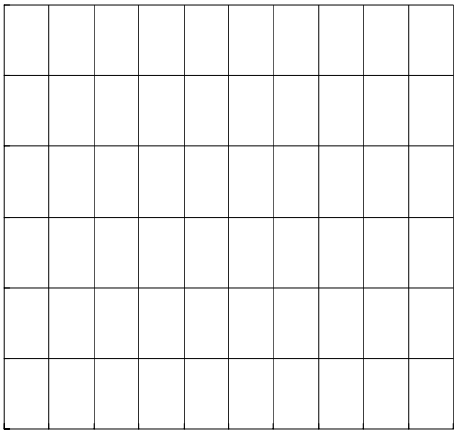
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F =2.0A(T_C=25)		0.82		V
		I_F =2.0A(T_C=125)		0.68		V
		I_F =6.0A(T_C=25)		0.92	1.0	V
		I_F =6.0A(T_C=125)		0.82	0.9	V
Instantaneous Reverse Current	I_R	V_R=200V(T_a=25)			10	A
		V_R=200V(T_a=125)			150	A
Reverse Recovery Time	t_{rr}	I_F=0.5A I_R=1.0A I_{RR}=0.25A			35	ns

/Notes

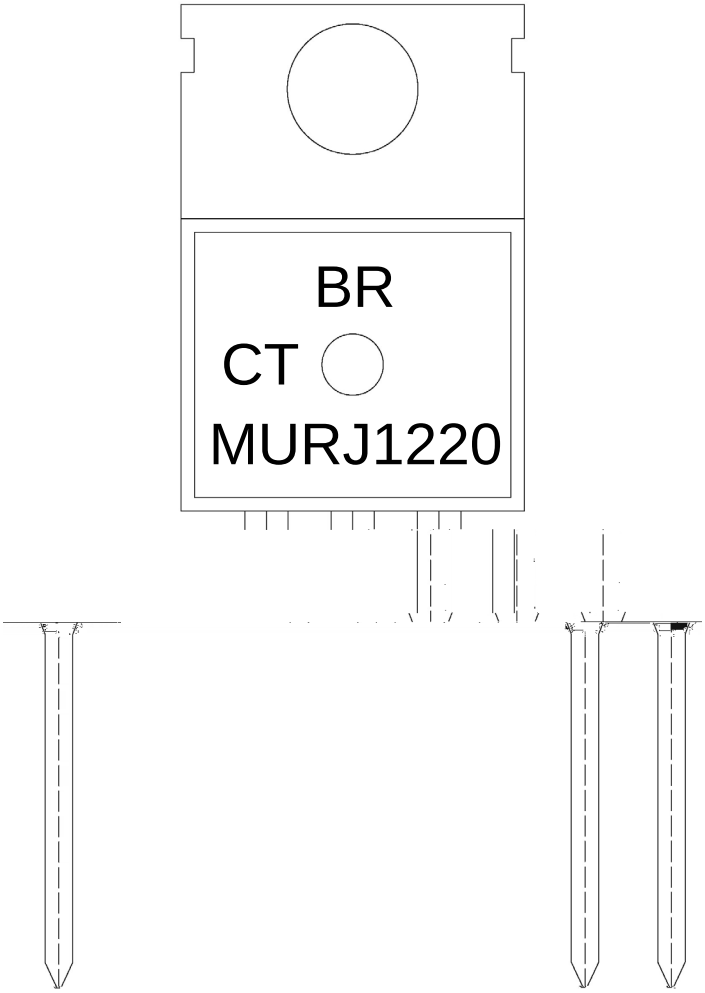
1. /Short duration pulse test used to minimize self-heating effect.
2. / Unless otherwise noted, values for the parameters of a single chip

/ Electrical Characteristic Curve





/ Marking Instructions



BR

MURJ1220

CT:

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Note:

BR:	Company Code
MURJ1220	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.